

In the Claims:

✓ Please cancel claims 57-60 without prejudice.

[Please amend the claims as follows]

*Sub G2*  
17. (Amended) An active matrix liquid crystal display comprising:

a plurality of pixel TFTs arranged in rows and columns over a TFT substrate and arrayed in a matrix;

driver TFTs formed over said TFT substrate and forming a driver circuit for driving said pixel TFTs;

*EI*  
a bus line provided over said TFT substrate and connected with at least one of said pixel TFTs, said bus line having a part located adjacent to a side edge of said TFT substrate;

a layer of a liquid crystal material with which said pixel TFTs and driver TFTs are in contact directly or via a thin film;

a counter substrate located opposite to said TFT substrate;

a nonconductive or weakly conductive material applied or adhesively bonded to a side edge of said counter substrate and [a] said side edge of said TFT substrate and said part of said bus line;

*F1*  
*Ent.*

a sealing material provided between said TFT substrate and said counter substrate and inside said side edge of said counter substrate and said side edge of said TFT substrate; and

a control circuit provided under and in contact with said sealing material.

*Sub G3*

21. (Amended) An active matrix liquid crystal display comprising:

*F2*

a plurality of pixel TFTs arranged in rows and columns over a TFT substrate and arrayed in a matrix;

driver TFTs formed over said TFT substrate and forming a driver circuit for driving said pixel TFTs;

a bus line provided over said TFT substrate and connected with at least one of said pixel TFTs, said bus line having a part located adjacent to a side edge of said TFT substrate;

a layer of a liquid crystal material with which said pixel TFTs and driver TFTs are in contact directly or via a thin film;

a counter substrate located opposite to said TFT substrate;

a nonconductive or weakly conductive material applied or adhesively bonded to a side edge of said counter substrate and [a] said side edge of said TFT substrate and said part of said bus line;

a sealing material provided between said TFT substrate and said counter substrate and inside said side edge of said counter

substrate and said side edge of said TFT substrate; and  
a control circuit provided under and in contact with said  
sealing material for controlling said driver circuit.

*F2*  
22. (Amended) An active matrix liquid crystal display  
comprising:

*Cmt.* a plurality of pixel TFTs arranged in rows and columns over  
a TFT substrate and arrayed in a matrix;

driver TFTs formed over said TFT substrate and forming a  
driver circuit for driving said pixel TFTs;

a bus line provided over said TFT substrate and connected  
with at least one of said pixel TFTs, said bus line having a  
part located adjacent to a side edge of said TFT substrate;

a layer of a liquid crystal material with which said pixel  
TFTs and driver TFTs are in contact directly or via a thin film;

a counter substrate located opposite to said TFT substrate;

a nonconductive or weakly conductive material applied or  
adhesively bonded to a side edge of said counter substrate and  
[a] said side edge of said TFT substrate and said part of said  
bus line;

a sealing material provided between said TFT substrate and  
said counter substrate and inside said side edge of said counter  
substrate and said side edge of said TFT substrate, said sealing  
material being provided outside at least said pixel TFTs; and

a control circuit provided under and in contact with said sealing material for controlling said driver circuit.

23. (Amended) An active matrix liquid crystal display comprising:

a plurality of pixel TFTs arranged in rows and columns over a TFT substrate and arrayed in a matrix;

driver TFTs formed over said TFT substrate and forming a driver circuit for driving said pixel TFTs;

a bus line provided over said TFT substrate and connected with at least one of said pixel TFTs, said bus line having a part located adjacent to a side edge of said TFT substrate;

a layer of a liquid crystal material with which said pixel TFTs and driver TFTs are in contact directly or via a thin film;

a counter substrate located opposite to said TFT substrate;

a nonconductive or weakly conductive material applied or adhesively bonded to a side edge of said counter substrate and [a] said side edge of said TFT substrate and said part of said bus line;

a sealing material provided between said TFT substrate and said counter substrate and inside said side edge of said counter substrate and said side edge of said TFT substrate, said sealing material being provided outside said pixel TFTs and said driver TFTs; and

a control circuit provided under and in contact with said sealing material for controlling said driver circuit.

24. (Amended) A method of fabricating an active matrix liquid crystal display comprising:

a plurality of pixel TFTs arranged in rows and columns over a TFT substrate and arrayed in a matrix;

driver TFTs formed over said TFT substrate and forming a driver circuit for driving said pixel TFTs;

a bus line provided over said TFT substrate and connected with at least one of said pixel TFTs;

a layer of a liquid crystal material with which said pixel TFTs and driver TFTs are in contact directly or via a thin film;

a counter substrate located opposite to said TFT substrate;

a sealing material provided between said TFT substrate and said counter substrate and outside at least said pixel TFTs; and

a control circuit provided under and in contact with said sealing material for controlling said driver circuit,

said method comprising:

cutting said TFT substrate and said counter substrate and said bus line outside said sealing material having said control circuit under and in contact with said sealing material; and

applying or adhesively bonding a nonconductive or weakly conductive material to the cut side edge of said TFT substrate

and the cut side edge of said counter substrate and the cut side  
edge of said bus line.

25. (Amended) A method of fabricating an active matrix liquid crystal display comprising:

a plurality of pixel TFTs arranged in rows and columns over a TFT substrate and arrayed in a matrix;

driver TFTs formed over said TFT substrate and forming a driver circuit for driving said pixel TFTs;

*F2*  
a bus line provided over said TFT substrate and connected  
with at least one of said pixel TFTs;

*Cont.*  
a layer of a liquid crystal material with which said pixel TFTs and driver TFTs are in contact directly or via a thin film;

a counter substrate located opposite to said TFT substrate;

a sealing material provided between said TFT substrate and said counter substrate and outside said pixel TFTs and said driver TFTs; and

a control circuit provided under and in contact with said sealing material for controlling said driver circuit,

said method comprising:

cutting said TFT substrate and said counter substrate and  
said bus line outside said sealing material having said control circuit under and in contact with said sealing material; and

applying or adhesively bonding a nonconductive or weakly

*F2*  
*cont.*  
conductive material to the cut side edge of said TFT substrate and the cut side edge of said counter substrate and the cut side edge of said bus line.

[Please add the following new claims.]

*Sub  
F64*

61. (New) A semiconductor device comprising:  
a pixel TFT provided over a TFT substrate;  
a counter substrate located opposite to said TFT substrate;  
a bus line provided over said TFT substrate and connected with said pixel TFT, said bus line having a part located adjacent to a side edge of said TFT substrate;  
a sealing material provided between said TFT substrate and said counter substrate; and  
a nonconductive material applied to a side edge of said counter substrate and said side edge of said TFT substrate and said part of said bus line,  
wherein said nonconductive material is provided on an outer side of said sealing material.

62. (New) A semiconductor device comprising:  
a pixel TFT provided over a TFT substrate;  
a counter substrate located opposite to said TFT substrate;

a bus line provided over said TFT substrate and connected with said pixel TFT, said bus line having a part located adjacent to a side edge of said TFT substrate;

a sealing material provided between said TFT substrate and said counter substrate; and

a weakly conductive material applied to a side edge of said counter substrate and said side edge of said TFT substrate and said part of said bus line,

wherein said weakly conductive material is provided on an outer side of said sealing material.

*F3*  
*Cmt.*  
63. (New) A semiconductor device comprising:

a pixel TFT provided over a TFT substrate;

a driver TFT provided over said TFT substrate;

a layer of a liquid crystal material with which said pixel TFT and said driver TFT are in contact directly or via a thin film;

a counter substrate located opposite to said TFT substrate with said layer of the liquid crystal material therebetween;

a bus line provided over said TFT substrate and connected with said pixel TFT, said bus line having a part located adjacent to a side edge of said TFT substrate;

a sealing material provided between said TFT substrate and said counter substrate; and

a nonconductive material applied to a side edge of said counter substrate and said side edge of said TFT substrate and said part of said bus line,

wherein said nonconductive material is provided on an outer side of said sealing material.

64. (New) A semiconductor device comprising:

a pixel TFT provided over a TFT substrate;

a driver TFT provided over said TFT substrate;

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Cmt.  
a layer of a liquid crystal material with which said pixel TFT and said driver TFT are in contact directly or via a thin film;

a counter substrate located opposite to said TFT substrate with said layer of the liquid crystal material therebetween;

a bus line provided over said TFT substrate and connected with said pixel TFT, said bus line having a part located adjacent to a side edge of said TFT substrate;

a sealing material provided between said TFT substrate counter substrate; and

a weakly conductive material applied to a side edge of said counter substrate and said side edge of said TFT substrate and said part of said bus line,

wherein said weakly conductive material is provided on an outer side of said sealing material.

65. (New) The display of claim 17 wherein said part of said bus line is aligned with said side edge of said counter substrate and said side edge of said TFT substrate.

66. (New) The display of claim 21 wherein said part of said bus line is aligned with said side edge of said counter substrate and said side edge of said TFT substrate.

67. (New) The display of claim 22 wherein said part of said bus line is aligned with said side edge of said counter substrate and said side edge of said TFT substrate.

68. (New) The display of claim 23 wherein said part of said bus line is aligned with said side edge of said counter substrate and said side edge of said TFT substrate.

69. (New) The display of claim 61 wherein said part of said bus line is aligned with said side edge of said counter substrate and said side edge of said TFT substrate.

70. (New) The display of claim 62 wherein said part of said bus line is aligned with said side edge of said counter substrate and said side edge of said TFT substrate.